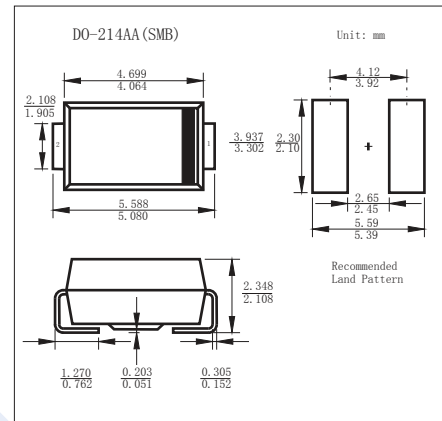


Schottky Diodes

SS32 ~ SS320

■ Features

- Metal silicon junction, majority carrier conduction
- For surface mounted applications
- Low power loss, high efficiency
- High forward surge current capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications



■ Absolute Maximum Ratings and Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Parameter	Symbol	SS 32	SS 33	SS 34	SS 35	SS 36	SS 38	SS 310	SS 315	SS 320	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	20	30	40	50	60	80	100	150	200	V
Maximum RMS voltage	V_{RMS}	14	21	28	35	42	56	70	105	140	
Maximum DC Blocking Voltage	V_{DC}	20	30	40	50	60	80	100	150	200	
Maximum average forward rectified current at T_L (see fig.1)	$I_{(AV)}$	3.0									A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	70.0									
Instantaneous Forward Voltage at 3A	V_F	0.55		0.70		0.85		0.95			V
Maximum DC Reverse Current at rated DC blocking voltage	I_R	0.5							1		mA
		20		10							
Typical Junction Capacitance *1	C_j	500			300					pF	
Typical thermal resistance *2	R_{thJA}	55						62			°C/W
Operating junction temperature range	T_j	-65 to 125			-65 to 150					°C	
Storage Temperature range	T_{stg}	-65 to 150									

* 1 Measured at 1MHz and applied reverse voltage of 4V D.C

* 2 P.C.B. mounted with 2" × 2" (5×5 cm) copper pad areas.

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Typical Characteristics

